

RECEIVED
CENTRAL FAX CENTER

JUL 06 2007

Amendment under 37 C.F.R. 1.111
U.S. Application No. 10/772,586
Docket No. 740756-2707
Page 2

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring by ejecting a first solution comprising a conductive material using a first solution ejector ~~for ejecting a conductive material~~ with moving the first solution ejector,

forming a resist mask by ejecting a second solution comprising a resist material on the wiring using a second solution ejector with moving the second solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

2. (Canceled)

3. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring,

forming a resist mask at least on the wiring by ejecting a solution comprising a resist material using a solution ejector with moving the solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

4. (Currently Amended) The method for producing the semiconductor device in ~~any one of claim 1 and claim 3,~~ wherein the first solution ejector has one or more of solution ejection ports.

Amendment under 37 C.F.R. 1.111

U.S. Application No. 10/772,586

Docket No. 740756-2707

Page 3

5. (Currently Amended) The method for producing the semiconductor device in ~~any one of claim 1 and claim 3, wherein when a wiring material, or a resist, or the like~~ the first solution is ejected using the first solution ejector, a substrate is heated.

6. (Previously Presented) The method for producing the semiconductor device in any one of claim 1 and claim 3, wherein the etching and/or ashing are/is processed at the atmospheric pressure or near-atmospheric pressure.

7. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a first solution ejector for ejecting a conductive material,
forming a resist mask on the wiring using a second solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

8. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a solution ejector for ejecting a conductive material,
forming a resist mask at least on the wiring, and
etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

9. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring,
forming a resist mask at least on the wiring using a solution ejector, and
etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

Amendment under 37 C.F.R. 1.111

U.S. Application No. 10/772,586

Docket No. 740756-2707

Page 4

10. (Withdrawn) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 9, wherein the solution ejector has one or more of solution ejection ports.

11. (Withdrawn) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 9, wherein when a solution is ejected using the solution ejector, a substrate is heated.

12. (Withdrawn) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 8, wherein the etching and/or the ashing are/is processed at the atmospheric pressure or near-atmospheric pressure.

13. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring by ejecting a first solution comprising a conductive material using a first solution ejector ~~for ejecting a conductive material~~ with moving the first solution ejector,

forming a resist mask by ejecting a second solution comprising a resist material on the wiring using a second solution ejector with moving the second solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

14. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring by ejecting a solution comprising a conductive material using a solution ejector ~~for ejecting a conductive material~~ with moving the solution ejector,

forming a resist mask at least on the wiring, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

Amendment under 37 C.F.R. 1.111
U.S. Application No. 10/772,586
Docket No. 740756-2707
Page 5

15. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring,

forming a resist mask at least on the wiring by ejecting a solution comprising a resist material using a solution ejector with moving the solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

16. (Currently Amended) The method for producing the semiconductor device in ~~any one of claim 13 to claim 15~~, wherein the first solution ejector has one or more of solution ejection ports.

17. (Currently Amended) The method for producing the semiconductor device in ~~any one of claim 13 to claim 15~~, wherein when ~~a wiring material~~ the first solution, or a resist, or the like is ejected using the first solution ejector, a substrate is heated.

18. (Previously presented) The method for producing the semiconductor device in any one of claim 13 to claim 15, wherein the etching is processed at the atmospheric pressure or near-atmospheric pressure.

19. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a first solution ejector for ejecting a conductive material,

forming a resist mask on the wiring using a second solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

Amendment under 37 C.F.R. 1.111
U.S. Application No. 10/772,586
Docket No. 740756-2707
Page 6

20. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a solution ejector for ejecting a conductive material,
forming a resist mask at least on the wiring, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

21. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring,

forming a resist mask at least on the wiring using a solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

22. (Withdrawn) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, wherein the solution ejector has one or more of solution ejection ports.

23. (Withdrawn) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, wherein when a solution is ejected using the solution ejector, a substrate is heated.

24. (Withdrawn) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, wherein the etching is processed at the atmospheric pressure or near-atmospheric pressure.

25. (New) The method for producing the semiconductor device in claim 1, wherein the second solution ejector has one or more of solution ejection ports.

Amendment under 37 C.F.R. 1.111
U.S. Application No. 10/772,586
Docket No. 740756-2707
Page 7

26. (New) The method for producing the semiconductor device in claim 3, wherein the solution ejector has one or more of solution ejection ports.

27. (New) The method for producing the semiconductor device in claim 1, wherein when the second solution is ejected using the second solution ejector, a substrate is heated.

28. (New) The method for producing the semiconductor device in claim 3, wherein when the solution is ejected using the solution ejector, a substrate is heated.

29. (New) The method for producing the semiconductor device in claim 13, wherein the second solution ejector has one or more of solution ejection ports.

30. (New) The method for producing the semiconductor device in claim 14 or 15, wherein the solution ejector has one or more of solution ejection ports.

31. (New) The method for producing the semiconductor device in claim 13, wherein when the second solution is ejected using the second solution ejector, a substrate is heated.

32. (New) The method for producing the semiconductor device in claim 14 or 15, wherein when the solution is ejected using the solution ejector, a substrate is heated.